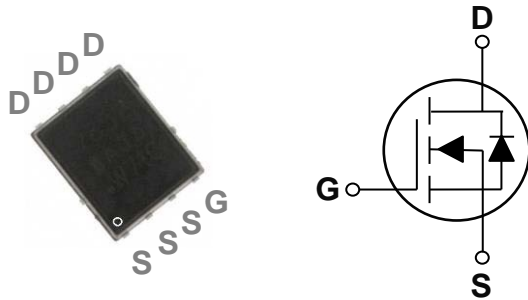


60V N-Channel MOSFETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

PPAK5X6 Pin Configuration



BVDSS	RDSON	ID
60V	2mΩ	140A

Features

- 60V, 140A, $R_{DS(ON)} = 2m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	140	A
	Drain Current – Continuous ($T_c=100^\circ C$)	88	A
I_{DM}	Drain Current – Pulsed ¹	560	A
EAS	Single Pulse Avalanche Energy ²	423	mJ
IAS	Single Pulse Avalanche Current ²	92	A
P_D	Power Dissipation ($T_c=25^\circ C$)	110	W
	Power Dissipation – Derate above $25^\circ C$	0.89	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.12	$^\circ C/W$



FTK6990DFN56

60V N-Channel MOSFETs

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_J=125^{\circ}\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$	---	1.7	2	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	2.5	3.2	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.7	2.5	V
gfs	Forward Transconductance	$V_{DS}=10V, I_D=3A$	---	15	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{3, 4}	$V_{DS}=30V, V_{GS}=10V, I_D=50A$	---	98	140	nC
Q_{gs}	Gate-Source Charge ^{3, 4}		---	24	36	
Q_{gd}	Gate-Drain Charge ^{3, 4}		---	27	40	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}	$V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	19	38	ns
T_r	Rise Time ^{3, 4}		---	12	24	
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		---	62	124	
T_f	Fall Time ^{3, 4}		---	130	260	
C_{iss}	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, F=1\text{MHz}$	---	4947	7400	pF
C_{oss}	Output Capacitance		---	2850	4200	
C_{rss}	Reverse Transfer Capacitance		---	26	40	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	1.1	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V, \text{Force Current}$	---	---	140	A
I_{SM}	Pulsed Source Current		---	---	280	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	---	---	1	V
T_{rr}	Reverse Recovery Time	$V_{GS}=10V, I_S=10A,$	---	88	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	175	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=92A, R_G=25\Omega, \text{Starting } T_J=25^{\circ}\text{C}.$
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

60V N-Channel MOSFETs

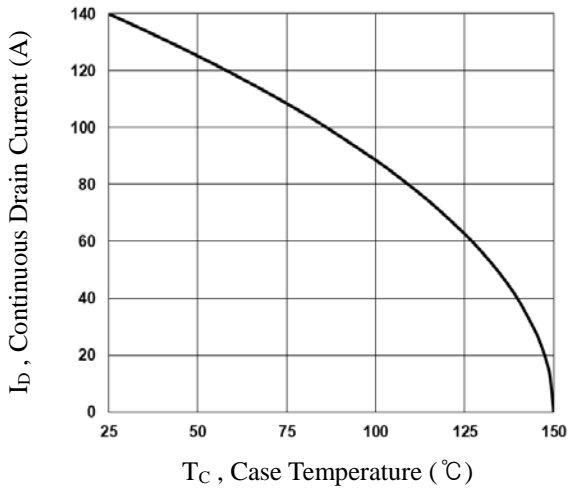


Fig.1 Continuous Drain Current vs. TC

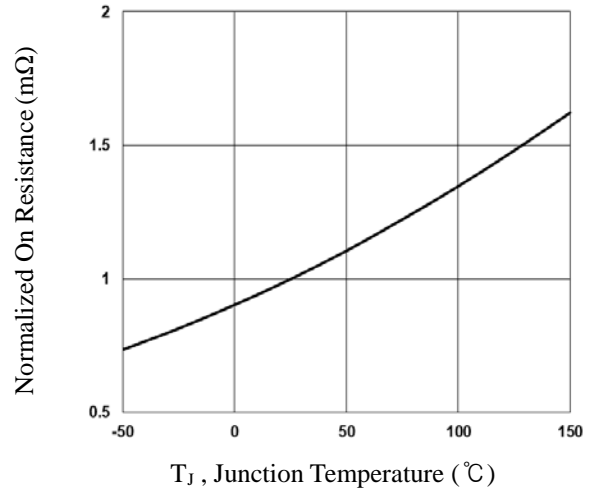


Fig.2 Normalized RDSON vs. TJ

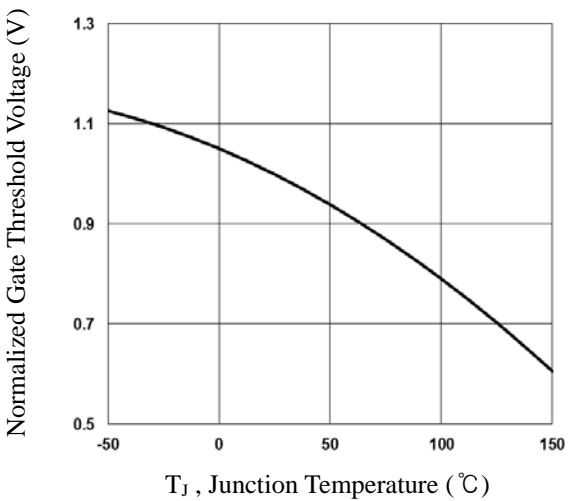


Fig.3 Normalized V_{th} vs. T_J

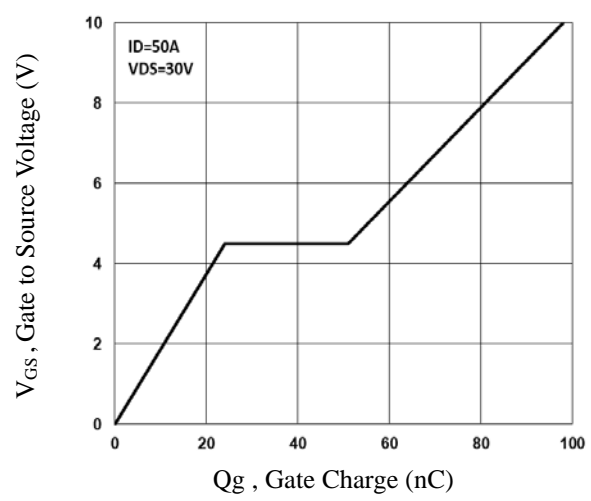


Fig.4 Gate Charge Characteristics

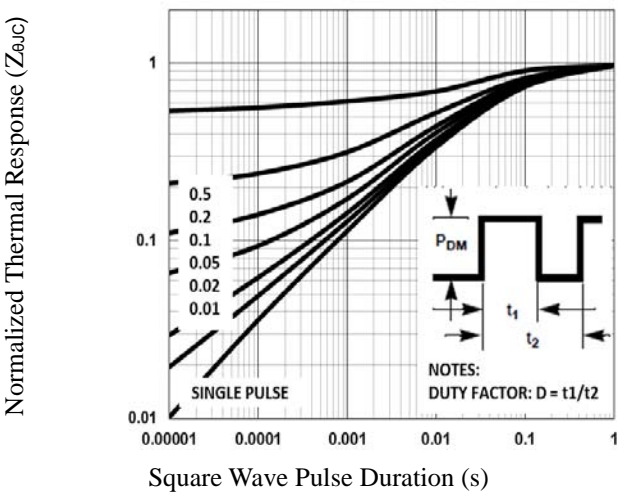


Fig.5 Normalized Transient Impedance

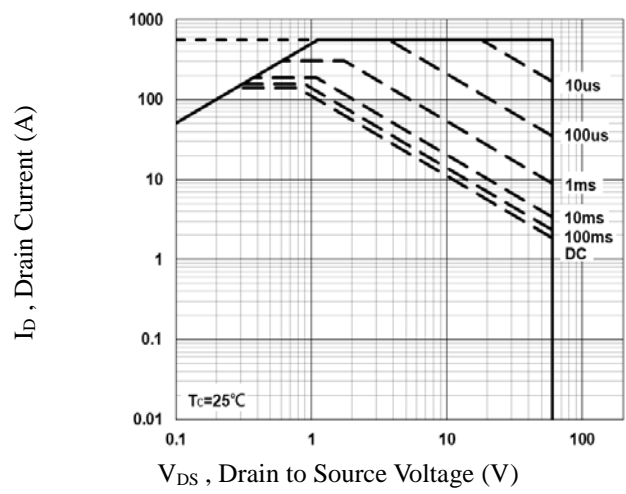


Fig.6 Maximum Safe Operation Area

60V N-Channel MOSFETs

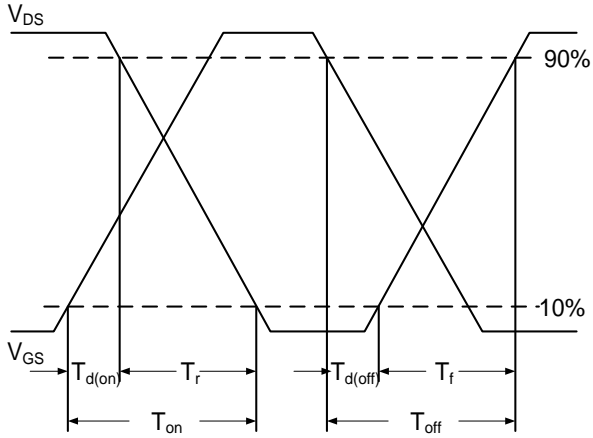


Fig.7 Switching Time Waveform

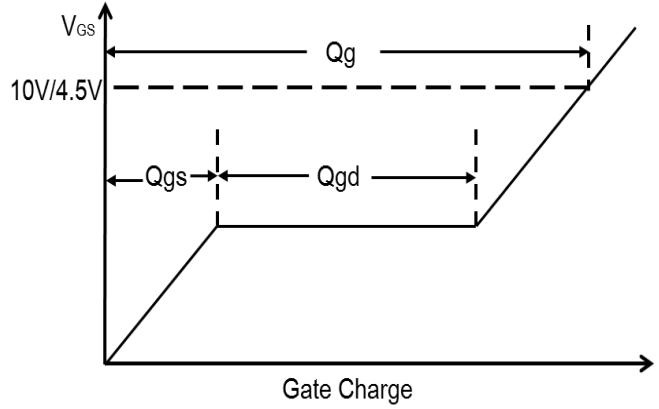
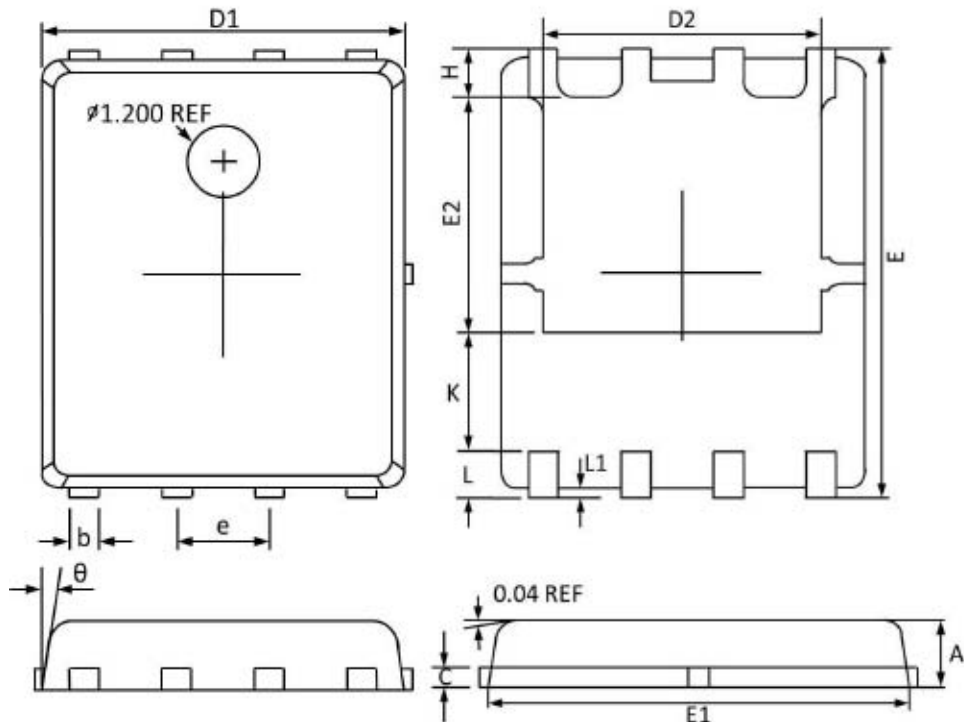


Fig.8 Gate Charge Waveform

60V N-Channel MOSFETs

PPAK5X6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
θ	12°	0°	12°	0°